

1. Scope :

This specification applies to P/N silicon zener diode chips,
Device NO. SD-108A6G

2. Structure :

- 2-1. Planar type : P/N Diode
- 2-2. Electrodes :
Top side : Gold pad.
Back side : Gold layer.

3. Size :

- 3-1. ^{※1} Chip size : 8.5 mils x 8.5 mils (0.215 mm x 0.215 mm).
- 3-2. Chip thickness : 6.0 ± 1.0 mils (0.150 ± 0.0254 mm)
- 3-3. Active area : 5.3 mils x 5.3 mils (0.135 mm x 0.135 mm).
- 3-4. ^{※2} Bonding pad : 5.9 mils x 5.9 mils (0.150 mm x 0.150 mm) .
- 3-5. Pattern drawing : Refer to the attached drawing.

^{※1} Including scribing line. The chip size is about (0.190±0.015)²mm² after dicing.

^{※2} The bonding pad dimension is (0.150±0.005)²mm² after etching.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I _R	V _R =20V E _e =0mW/cm ²			500	nA
Zener Voltage	V _Z	I _Z =5mA E _e =0mW/cm ²	22		32	V
Forward Voltage	V _f	I _F =20mA E _e =0mW/cm ²	0.75		1.2	V

